

TSMC-01-725



2812
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April 3, 2002

To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/081,985 02/21/2002

Zhi-Cherng Lu et al.

ADJUSTMENT OF N AND K VALUES IN
A DARC FILM

Grp. Art Unit: 2812

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner of Patents and
Trademarks, Washington, D.C. 20231, on April 10, 2002.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 4/10/02

U.S. Patent 6,291,363 to Yin et al., "Surface Treatment of DARC Films to Reduce Defects in Subsequent Cap Layers," discloses an ammonia based treatment of a dielectric anti-reflective coating (DARC) layer to minimize formation of defects therein.

U.S. Patent 6,228,700 to Lee, "Method for Manufacturing Dynamic Random Access Memory," discloses a SION or SIOX DARC layer process.

U.S. Patent 6,063,704 to Demirlioglu, "Process for Incorporating Silicon Oxynitride DARC Layer into Formation of Silicide Polysilicon Contact," discloses a silicon oxynitride dielectric anti-reflective coating layer process wherein a DARC is given added silicon so that it can be used in a SALICIDE process.

U.S. Patent 6,060,132 to Lee, "High Density Plasma CVD Process for Making Dielectric Anti-reflective Coatings," discloses a chemical vapor deposition dielectric anti-reflective coating layer process and uses a plasma treatment to remove contamination by a resist.

Sincerely,


Stephen B. Ackerman, Reg. #37761

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

Document Number (Specie

TSMC-01-72

10/081, 985

Appleton -

Eni-Cherng Lin et al.

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U. S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.